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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	18432
Number of I/O	91
Number of Gates	60000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	144-LQFP
Supplier Device Package	144-TQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3p060-2tq144

I/O Power-Up and Supply Voltage Thresholds for Power-On Reset (Commercial and Industrial)

Sophisticated power-up management circuitry is designed into every ProASIC®3 device. These circuits ensure easy transition from the powered-off state to the powered-up state of the device. The many different supplies can power up in any sequence with minimized current spikes or surges.

In addition, the I/O will be in a known state through the power-up sequence. The basic principle is shown in [Figure 2-2 on page 2-5](#).

There are five regions to consider during power-up.

ProASIC3 I/Os are activated only if ALL of the following three conditions are met:

1. VCC and VCCI are above the minimum specified trip points ([Figure 2-2 on page 2-5](#)).
2. VCCI > VCC – 0.75 V (typical)
3. Chip is in the operating mode.

VCCI Trip Point:

Ramping up: $0.6\text{ V} < \text{trip_point_up} < 1.2\text{ V}$

Ramping down: $0.5\text{ V} < \text{trip_point_down} < 1.1\text{ V}$

VCC Trip Point:

Ramping up: $0.6\text{ V} < \text{trip_point_up} < 1.1\text{ V}$

Ramping down: $0.5\text{ V} < \text{trip_point_down} < 1\text{ V}$

VCC and VCCI ramp-up trip points are about 100 mV higher than ramp-down trip points. This specifically built-in hysteresis prevents undesirable power-up oscillations and current surges. Note the following:

- During programming, I/Os become tristated and weakly pulled up to VCCI.
- JTAG supply, PLL power supplies, and charge pump VPUMP supply have no influence on I/O behavior.

PLL Behavior at Brownout Condition

Microsemi recommends using monotonic power supplies or voltage regulators to ensure proper power-up behavior. Power ramp-up should be monotonic at least until VCC and VCCPLLX exceed brownout activation levels. The VCC activation level is specified as 1.1 V worst-case (see [Figure 2-2 on page 2-5](#) for more details).

When PLL power supply voltage and/or VCC levels drop below the VCC brownout levels ($0.75\text{ V} \pm 0.25\text{ V}$), the PLL output lock signal goes low and/or the output clock is lost. Refer to the "Power-Up/Down Behavior of Low Power Flash Devices" chapter of the *ProASIC3 FPGA Fabric User's Guide* for information on clock and lock recovery.

Internal Power-Up Activation Sequence

1. Core
2. Input buffers

Output buffers, after 200 ns delay from input buffer activation.

Thermal Characteristics

Introduction

The temperature variable in the Microsemi Designer software refers to the junction temperature, not the ambient temperature. This is an important distinction because dynamic and static power consumption cause the chip junction to be higher than the ambient temperature.

EQ can be used to calculate junction temperature.

$$T_J = \text{Junction Temperature} = \Delta T + T_A$$

where:

T_A = Ambient Temperature

ΔT = Temperature gradient between junction (silicon) and ambient $\Delta T = \theta_{ja} * P$

θ_{ja} = Junction-to-ambient of the package. θ_{ja} numbers are located in [Table 2-5 on page 2-6](#).

P = Power dissipation

Table 2-29 • I/O Output Buffer Maximum Resistances¹
Applicable to Standard Plus I/O Banks

Standard	Drive Strength	R _{PULL-DOWN} (Ω) ²	R _{PULL-UP} (Ω) ³
3.3 V LVTTTL / 3.3 V LVCMOS	2 mA	100	300
	4 mA	100	300
	6 mA	50	150
	8 mA	50	150
	12 mA	25	75
	16 mA	25	75
3.3 V LVCMOS Wide Range ⁴	100 μA	Same as regular 3.3 V LVCMOS	Same as regular 3.3 V LVCMOS
2.5 V LVCMOS	2 mA	100	200
	4 mA	100	200
	6 mA	50	100
	8 mA	50	100
	12 mA	25	50
1.8 V LVCMOS	2 mA	200	225
	4 mA	100	112
	6 mA	50	56
	8 mA	50	56
1.5 V LVCMOS	2 mA	200	224
	4 mA	100	112
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	25	75

Notes:

1. These maximum values are provided for informational reasons only. Minimum output buffer resistance values depend on VCCI, drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located at <http://www.microsemi.com/soc/download/ibis/default.aspx>.
2. $R_{(PULL-DOWN-MAX)} = (VOL_{spec}) / IOL_{spec}$
3. $R_{(PULL-UP-MAX)} = (VCCI_{max} - VOH_{spec}) / IOH_{spec}$
4. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.

Table 2-42 • 3.3 V LVTTTL / 3.3 V LVCMOS Low Slew**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 3.0\text{ V}$** **Applicable to Advanced I/O Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	10.26	0.04	1.02	0.43	10.45	8.90	2.64	2.46	12.68	11.13	ns
	–1	0.56	8.72	0.04	0.86	0.36	8.89	7.57	2.25	2.09	10.79	9.47	ns
	–2	0.49	7.66	0.03	0.76	0.32	7.80	6.64	1.98	1.83	9.47	8.31	ns
4 mA	Std.	0.66	10.26	0.04	1.02	0.43	10.45	8.90	2.64	2.46	12.68	11.13	ns
	–1	0.56	8.72	0.04	0.86	0.36	8.89	7.57	2.25	2.09	10.79	9.47	ns
	–2	0.49	7.66	0.03	0.76	0.32	7.80	6.64	1.98	1.83	9.47	8.31	ns
6 mA	Std.	0.66	7.27	0.04	1.02	0.43	7.41	6.28	2.98	3.04	9.65	8.52	ns
	–1	0.56	6.19	0.04	0.86	0.36	6.30	5.35	2.54	2.59	8.20	7.25	ns
	–2	0.49	5.43	0.03	0.76	0.32	5.53	4.69	2.23	2.27	7.20	6.36	ns
8 mA	Std.	0.66	7.27	0.04	1.02	0.43	7.41	6.28	2.98	3.04	9.65	8.52	ns
	–1	0.56	6.19	0.04	0.86	0.36	6.30	5.35	2.54	2.59	8.20	7.25	ns
	–2	0.49	5.43	0.03	0.76	0.32	5.53	4.69	2.23	2.27	7.20	6.36	ns
12 mA	Std.	0.66	5.58	0.04	1.02	0.43	5.68	4.87	3.21	3.42	7.92	7.11	ns
	–1	0.56	4.75	0.04	0.86	0.36	4.84	4.14	2.73	2.91	6.74	6.05	ns
	–2	0.49	4.17	0.03	0.76	0.32	4.24	3.64	2.39	2.55	5.91	5.31	ns
16 mA	Std.	0.66	5.21	0.04	1.02	0.43	5.30	4.56	3.26	3.51	7.54	6.80	ns
	–1	0.56	4.43	0.04	0.86	0.36	4.51	3.88	2.77	2.99	6.41	5.79	ns
	–2	0.49	3.89	0.03	0.76	0.32	3.96	3.41	2.43	2.62	5.63	5.08	ns
24 mA	Std.	0.66	4.85	0.04	1.02	0.43	4.94	4.54	3.32	3.88	7.18	6.78	ns
	–1	0.56	4.13	0.04	0.86	0.36	4.20	3.87	2.82	3.30	6.10	5.77	ns
	–2	0.49	3.62	0.03	0.76	0.32	3.69	3.39	2.48	2.90	5.36	5.06	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-54 • 3.3 V LVTTTL / 3.3 V LVCMOS High Slew
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 3.0\text{ V}$
Applicable to Standard I/O Banks

Drive Strength	Equiv. Software Default Drive Strength Option ¹	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
100 μA	2 mA	Std.	0.60	10.93	0.04	1.52	0.43	10.93	9.46	3.20	3.32	ns
		–1	0.51	9.29	0.04	1.29	0.36	9.29	8.04	2.72	2.82	ns
		–2	0.45	8.16	0.03	1.13	0.32	8.16	7.06	2.39	2.48	ns
100 μA	4 mA	Std.	0.60	10.93	0.04	1.52	0.43	10.93	9.46	3.20	3.32	ns
		–1	0.51	9.29	0.04	1.29	0.36	9.29	8.04	2.72	2.82	ns
		–2	0.45	8.16	0.03	1.13	0.32	8.16	7.06	2.39	2.48	ns
100 μA	6 mA	Std.	0.60	6.82	0.04	1.52	0.43	6.82	5.70	3.70	4.16	ns
		–1	0.51	5.80	0.04	1.29	0.36	5.80	4.85	3.15	3.54	ns
		–2	0.45	5.09	0.03	1.13	0.32	5.09	4.25	2.77	3.11	ns
100 μA	8 mA	Std.	0.60	6.82	0.04	1.52	0.43	6.82	5.70	3.70	4.16	ns
		–1	0.51	5.80	0.04	1.29	0.36	5.80	4.85	3.15	3.54	ns
		–2	0.45	5.09	0.03	1.13	0.32	5.09	4.25	2.77	3.11	ns

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. Software default selection highlighted in gray.
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-73 • 1.8 V LVC MOS Low Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	14.80	0.04	1.20	0.43	13.49	14.80	2.25	1.46	15.73	17.04	ns
	–1	0.56	12.59	0.04	1.02	0.36	11.48	12.59	1.91	1.25	13.38	14.49	ns
	–2	0.49	11.05	0.03	0.90	0.32	10.08	11.05	1.68	1.09	11.75	12.72	ns
4 mA	Std.	0.66	9.90	0.04	1.20	0.43	9.73	9.90	2.65	2.50	11.97	12.13	ns
	–1	0.56	8.42	0.04	1.02	0.36	8.28	8.42	2.26	2.12	10.18	10.32	ns
	–2	0.49	7.39	0.03	0.90	0.32	7.27	7.39	1.98	1.86	8.94	9.06	ns
6 mA	Std.	0.66	7.44	0.04	1.20	0.43	7.58	7.32	2.94	2.99	9.81	9.56	ns
	–1	0.56	6.33	0.04	1.02	0.36	6.44	6.23	2.50	2.54	8.35	8.13	ns
	–2	0.49	5.55	0.03	0.90	0.32	5.66	5.47	2.19	2.23	7.33	7.14	ns
8 mA	Std.	0.66	7.44	0.04	1.20	0.43	7.58	7.32	2.94	2.99	9.81	9.56	ns
	–1	0.56	6.33	0.04	1.02	0.36	6.44	6.23	2.50	2.54	8.35	8.13	ns
	–2	0.49	5.55	0.03	0.90	0.32	5.66	5.47	2.19	2.23	7.33	7.14	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-74 • 1.8 V LVC MOS High Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V
Applicable to Standard I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.66	11.21	0.04	1.20	0.43	8.53	11.21	1.99	1.21	ns
	–1	0.56	9.54	0.04	1.02	0.36	7.26	9.54	1.69	1.03	ns
	–2	0.49	8.37	0.03	0.90	0.32	6.37	8.37	1.49	0.90	ns
4 mA	Std.	0.66	6.34	0.04	1.20	0.43	5.38	6.34	2.41	2.48	ns
	–1	0.56	5.40	0.04	1.02	0.36	4.58	5.40	2.05	2.11	ns
	–2	0.49	4.74	0.03	0.90	0.32	4.02	4.74	1.80	1.85	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Timing Characteristics

Table 2-80 • 1.5 V LVCMOS High Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 1.4\text{ V}$
 Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	8.36	0.04	1.44	0.43	6.82	8.36	3.39	2.77	9.06	10.60	ns
	–1	0.56	7.11	0.04	1.22	0.36	5.80	7.11	2.88	2.35	7.71	9.02	ns
	–2	0.49	6.24	0.03	1.07	0.32	5.10	6.24	2.53	2.06	6.76	7.91	ns
4 mA	Std.	0.66	5.31	0.04	1.44	0.43	4.85	5.31	3.74	3.40	7.09	7.55	ns
	–1	0.56	4.52	0.04	1.22	0.36	4.13	4.52	3.18	2.89	6.03	6.42	ns
	–2	0.49	3.97	0.03	1.07	0.32	3.62	3.97	2.79	2.54	5.29	5.64	ns
6 mA	Std.	0.66	4.67	0.04	1.44	0.43	4.55	4.67	3.82	3.56	6.78	6.90	ns
	–1	0.56	3.97	0.04	1.22	0.36	3.87	3.97	3.25	3.03	5.77	5.87	ns
	–2	0.49	3.49	0.03	1.07	0.32	3.40	3.49	2.85	2.66	5.07	5.16	ns
8 mA	Std.	0.66	4.08	0.04	1.44	0.43	4.15	3.58	3.94	4.20	6.39	5.81	ns
	–1	0.56	3.47	0.04	1.22	0.36	3.53	3.04	3.36	3.58	5.44	4.95	ns
	–2	0.49	3.05	0.03	1.07	0.32	3.10	2.67	2.95	3.14	4.77	4.34	ns
12 mA	Std.	0.66	4.08	0.04	1.44	0.43	4.15	3.58	3.94	4.20	6.39	5.81	ns
	–1	0.56	3.47	0.04	1.22	0.36	3.53	3.04	3.36	3.58	5.44	4.95	ns
	–2	0.49	3.05	0.03	1.07	0.32	3.10	2.67	2.95	3.14	4.77	4.34	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Output DDR Module

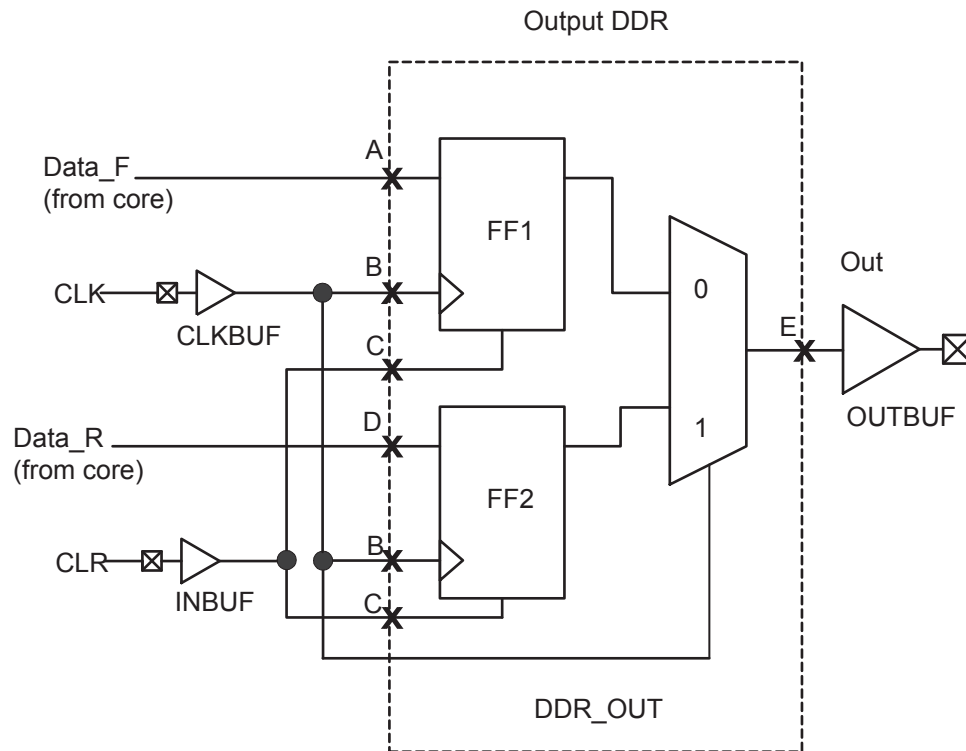


Figure 2-22 • Output DDR Timing Model

Table 2-103 • Parameter Definitions

Parameter Name	Parameter Definition	Measuring Nodes (from, to)
t_{DDROCLKQ}	Clock-to-Out	B, E
$t_{\text{DDROCLR2Q}}$	Asynchronous Clear-to-Out	C, E
$t_{\text{DDROREMCLR}}$	Clear Removal	C, B
$t_{\text{DDRORECCLR}}$	Clear Recovery	C, B
t_{DDROSUD1}	Data Setup Data_F	A, B
t_{DDROSUD2}	Data Setup Data_R	D, B
t_{DDROHD1}	Data Hold Data_F	A, B
t_{DDROHD2}	Data Hold Data_R	D, B

VersaTile Characteristics

VersaTile Specifications as a Combinatorial Module

The ProASIC3 library offers all combinations of LUT-3 combinatorial functions. In this section, timing characteristics are presented for a sample of the library. For more details, refer to the [Fusion](#), [IGLOO®/e](#), and [ProASIC3/E Macro Library Guide](#).

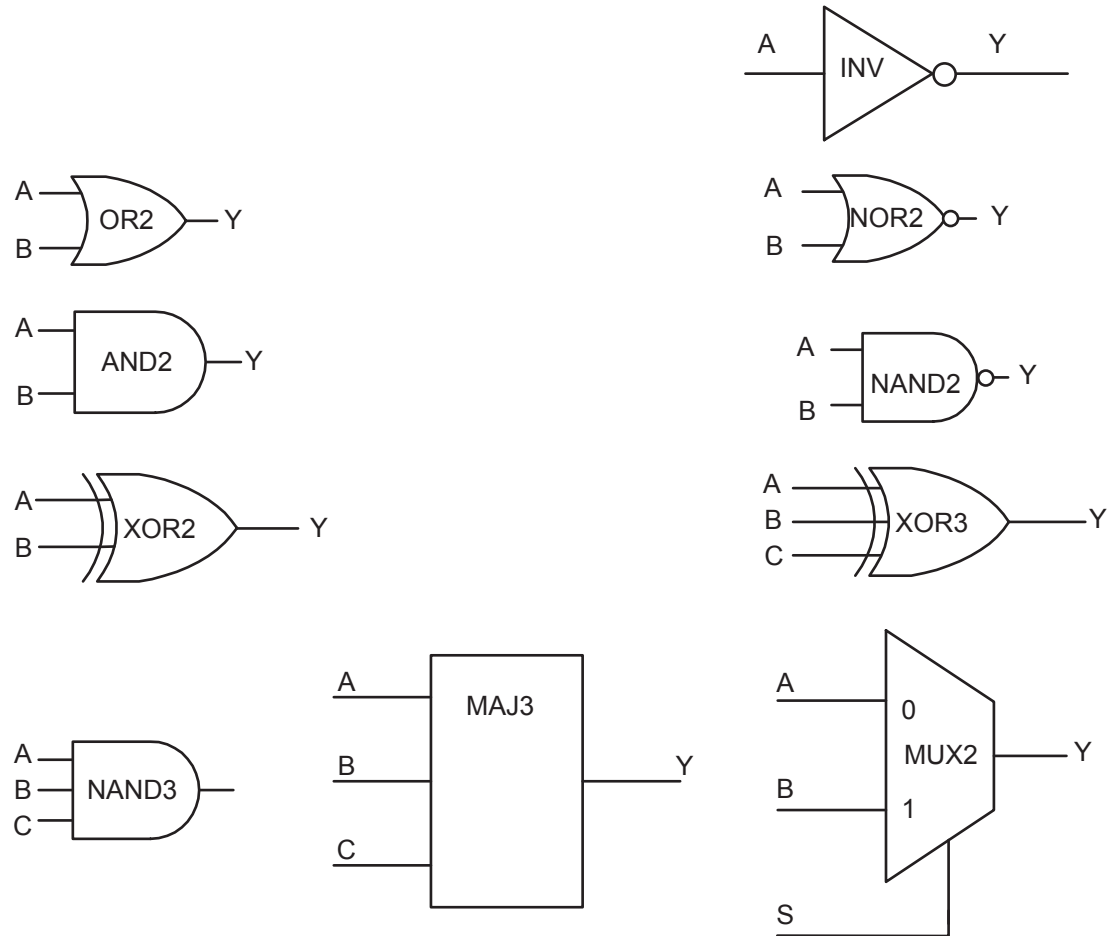


Figure 2-24 • Sample of Combinatorial Cells

Table 2-111 • A3P250 Global Resource
Commercial-Case Conditions: $T_J = 70^{\circ}\text{C}$, $V_{CC} = 1.425\text{ V}$

Parameter	Description	–2		–1		Std.		Units
		Min. ¹	Max. ²	Min. ¹	Max. ²	Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	0.80	1.01	0.91	1.15	1.07	1.36	ns
t_{RCKH}	Input High Delay for Global Clock	0.78	1.04	0.89	1.18	1.04	1.39	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	0.75		0.85		1.00		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	0.85		0.96		1.13		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.26		0.29		0.34	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-112 • A3P400 Global Resource
Commercial-Case Conditions: $T_J = 70^{\circ}\text{C}$, $V_{CC} = 1.425\text{ V}$

Parameter	Description	–2		–1		Std.		Units
		Min. ¹	Max. ²	Min. ¹	Max. ²	Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	0.87	1.09	0.99	1.24	1.17	1.46	ns
t_{RCKH}	Input High Delay for Global Clock	0.86	1.11	0.98	1.27	1.15	1.49	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	0.75		0.85		1.00		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	0.85		0.96		1.13		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.26		0.29		0.34	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Embedded SRAM and FIFO Characteristics

SRAM

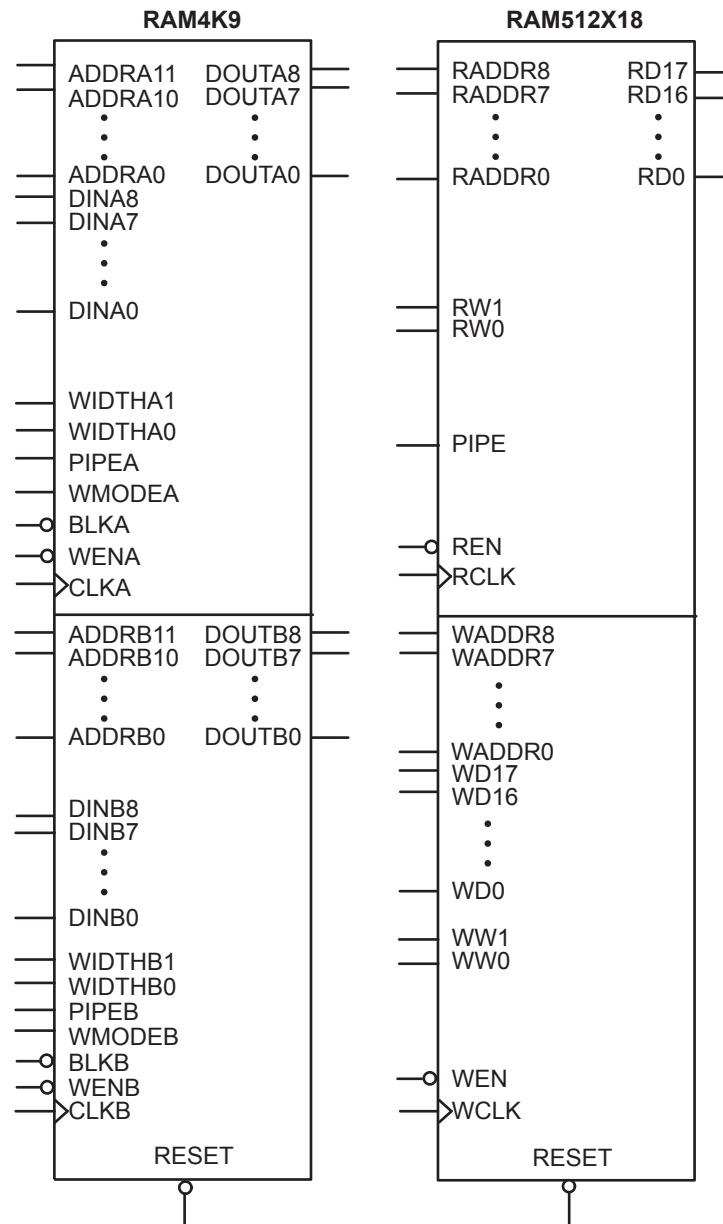


Figure 2-30 • RAM Models

Timing Characteristics

Table 2-116 • RAM4K9

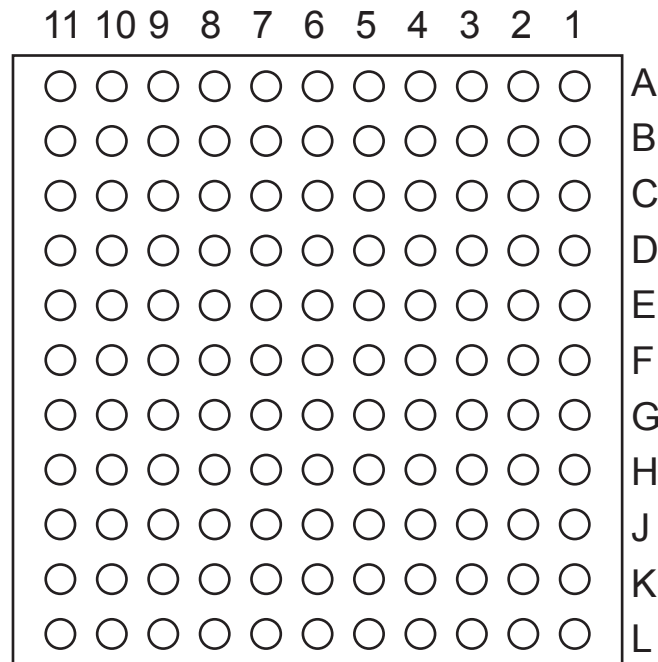
 Commercial-Case Conditions: $T_J = 70^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2	-1	Std.	Units
t_{AS}	Address setup time	0.25	0.28	0.33	ns
t_{AH}	Address hold time	0.00	0.00	0.00	ns
t_{ENS}	REN, WEN setup time	0.14	0.16	0.19	ns
t_{ENH}	REN, WEN hold time	0.10	0.11	0.13	ns
t_{BKS}	BLK setup time	0.23	0.27	0.31	ns
t_{BKH}	BLK hold time	0.02	0.02	0.02	ns
t_{DS}	Input data (DIN) setup time	0.18	0.21	0.25	ns
t_{DH}	Input data (DIN) hold time	0.00	0.00	0.00	ns
t_{CKQ1}	Clock High to new data valid on DOUT (output retained, WMODE = 0)	2.36	2.68	3.15	ns
	Clock High to new data valid on DOUT (flow-through, WMODE = 1)	1.79	2.03	2.39	ns
t_{CKQ2}	Clock High to new data valid on DOUT (pipelined)	0.89	1.02	1.20	ns
t_{C2CWWL}^1	Address collision clk-to-clk delay for reliable write after write on same address—Applicable to Closing Edge	0.33	0.28	0.25	ns
t_{C2CWWH}^1	Address collision clk-to-clk delay for reliable write after write on same address—Applicable to Rising Edge	0.30	0.26	0.23	ns
t_{C2CRWH}^1	Address collision clk-to-clk delay for reliable read access after write on same address—Applicable to Opening Edge	0.45	0.38	0.34	ns
t_{C2CWRH}^1	Address collision clk-to-clk delay for reliable write access after read on same address— Applicable to Opening Edge	0.49	0.42	0.37	ns
t_{RSTBQ}	RESET Low to data out Low on DOUT (flow-through)	0.92	1.05	1.23	ns
	RESET Low to Data Out Low on DOUT (pipelined)	0.92	1.05	1.23	ns
$t_{REMRSTB}$	RESET removal	0.29	0.33	0.38	ns
$t_{RECRSTB}$	RESET recovery	1.50	1.71	2.01	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.21	0.24	0.29	ns
t_{CYC}	Clock cycle time	3.23	3.68	4.32	ns
F_{MAX}	Maximum frequency	310	272	231	MHz

Notes:

1. For more information, refer to the application note [Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs](#).
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

CS121 – Bottom View

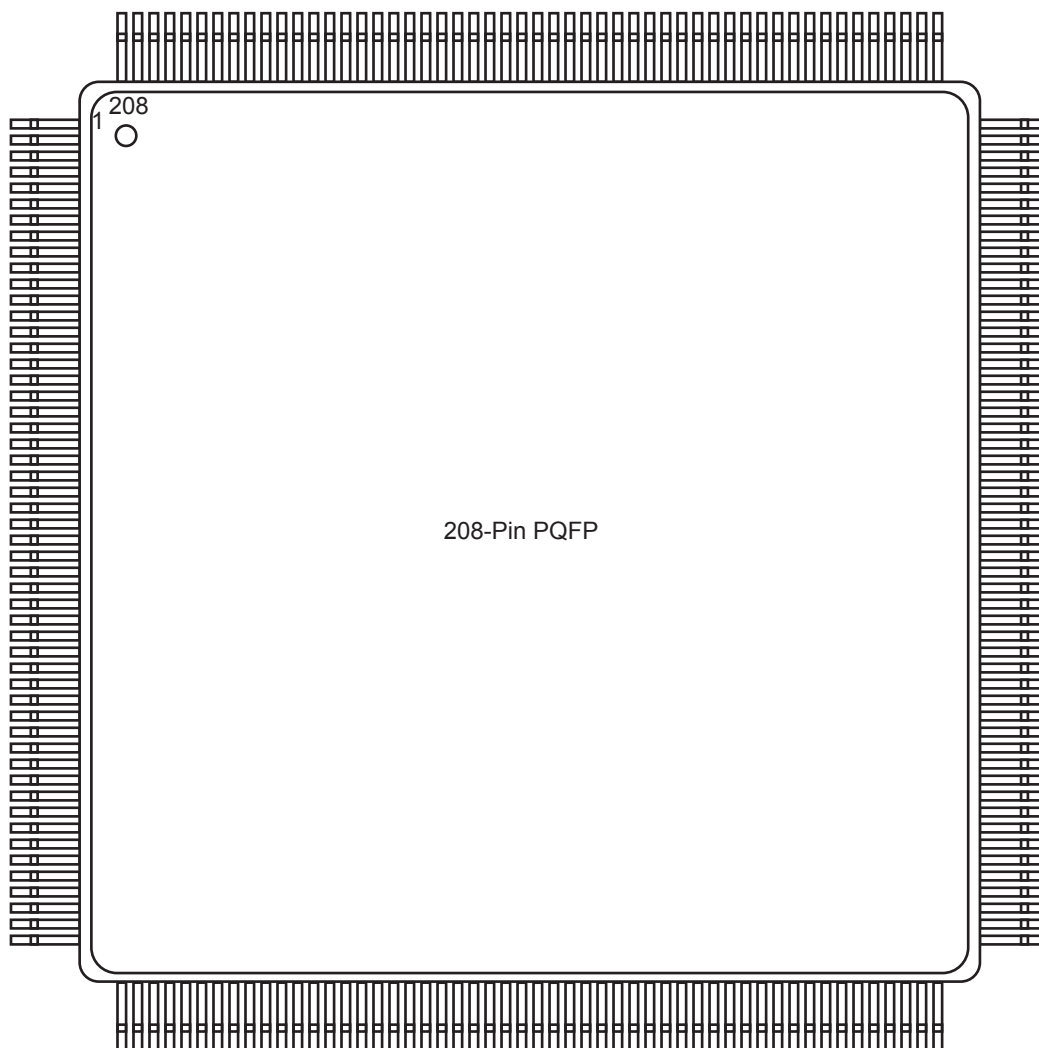


Note: The die attach paddle center of the package is tied to ground (GND).

Note

For more information on package drawings, see [PD3068: Package Mechanical Drawings](#).

PQ208 – Top View



Note

For more information on package drawings, see [PD3068: Package Mechanical Drawings](#).

PQ208	
Pin Number	A3P125 Function
109	TRST
110	VJTAG
111	GDA0/IO66RSB0
112	GDA1/IO65RSB0
113	GDB0/IO64RSB0
114	GDB1/IO63RSB0
115	GDC0/IO62RSB0
116	GDC1/IO61RSB0
117	NC
118	NC
119	NC
120	NC
121	NC
122	GND
123	VCCIB0
124	NC
125	NC
126	VCC
127	IO60RSB0
128	GCC2/IO59RSB0
129	GCB2/IO58RSB0
130	GND
131	GCA2/IO57RSB0
132	GCA0/IO56RSB0
133	GCA1/IO55RSB0
134	GCB0/IO54RSB0
135	GCB1/IO53RSB0
136	GCC0/IO52RSB0
137	GCC1/IO51RSB0
138	IO50RSB0
139	IO49RSB0
140	VCCIB0
141	GND
142	VCC
143	IO48RSB0
144	IO47RSB0

PQ208	
Pin Number	A3P125 Function
145	IO46RSB0
146	NC
147	NC
148	NC
149	GBC2/IO45RSB0
150	IO44RSB0
151	GBB2/IO43RSB0
152	IO42RSB0
153	GBA2/IO41RSB0
154	VMV0
155	GNDQ
156	GND
157	NC
158	GBA1/IO40RSB0
159	GBA0/IO39RSB0
160	GBB1/IO38RSB0
161	GBB0/IO37RSB0
162	GND
163	GBC1/IO36RSB0
164	GBC0/IO35RSB0
165	IO34RSB0
166	IO33RSB0
167	IO32RSB0
168	IO31RSB0
169	IO30RSB0
170	VCCIB0
171	VCC
172	IO29RSB0
173	IO28RSB0
174	IO27RSB0
175	IO26RSB0
176	IO25RSB0
177	IO24RSB0
178	GND
179	IO23RSB0
180	IO22RSB0

PQ208	
Pin Number	A3P125 Function
181	IO21RSB0
182	IO20RSB0
183	IO19RSB0
184	IO18RSB0
185	IO17RSB0
186	VCCIB0
187	VCC
188	IO16RSB0
189	IO15RSB0
190	IO14RSB0
191	IO13RSB0
192	IO12RSB0
193	IO11RSB0
194	IO10RSB0
195	GND
196	IO09RSB0
197	IO08RSB0
198	IO07RSB0
199	IO06RSB0
200	VCCIB0
201	GAC1/IO05RSB0
202	GAC0/IO04RSB0
203	GAB1/IO03RSB0
204	GAB0/IO02RSB0
205	GAA1/IO01RSB0
206	GAA0/IO00RSB0
207	GNDQ
208	VMV0

PQ208	
Pin Number	A3P600 Function
1	GND
2	GAA2/IO174PDB3
3	IO174NDB3
4	GAB2/IO173PDB3
5	IO173NDB3
6	GAC2/IO172PDB3
7	IO172NDB3
8	IO171PDB3
9	IO171NDB3
10	IO170PDB3
11	IO170NDB3
12	IO169PDB3
13	IO169NDB3
14	IO168PDB3
15	IO168NDB3
16	VCC
17	GND
18	VCCIB3
19	IO166PDB3
20	IO166NDB3
21	GFC1/IO164PDB3
22	GFC0/IO164NDB3
23	GFB1/IO163PDB3
24	GFB0/IO163NDB3
25	VCOMPLF
26	GFA0/IO162NPB3
27	VCCPLF
28	GFA1/IO162PPB3
29	GND
30	GFA2/IO161PDB3
31	IO161NDB3
32	GFB2/IO160PDB3
33	IO160NDB3
34	GFC2/IO159PDB3
35	IO159NDB3
36	VCC

PQ208	
Pin Number	A3P600 Function
37	IO152PDB3
38	IO152NDB3
39	IO150PSB3
40	VCCIB3
41	GND
42	IO147PDB3
43	IO147NDB3
44	GEC1/IO146PDB3
45	GEC0/IO146NDB3
46	GEB1/IO145PDB3
47	GEB0/IO145NDB3
48	GEA1/IO144PDB3
49	GEA0/IO144NDB3
50	VMV3
51	GNDQ
52	GND
53	VMV2
54	GEA2/IO143RSB2
55	GEB2/IO142RSB2
56	GEC2/IO141RSB2
57	IO140RSB2
58	IO139RSB2
59	IO138RSB2
60	IO137RSB2
61	IO136RSB2
62	VCCIB2
63	IO135RSB2
64	IO133RSB2
65	GND
66	IO131RSB2
67	IO129RSB2
68	IO127RSB2
69	IO125RSB2
70	IO123RSB2
71	VCC
72	VCCIB2

PQ208	
Pin Number	A3P600 Function
73	IO120RSB2
74	IO119RSB2
75	IO118RSB2
76	IO117RSB2
77	IO116RSB2
78	IO115RSB2
79	IO114RSB2
80	IO112RSB2
81	GND
82	IO111RSB2
83	IO110RSB2
84	IO109RSB2
85	IO108RSB2
86	IO107RSB2
87	IO106RSB2
88	VCC
89	VCCIB2
90	IO104RSB2
91	IO102RSB2
92	IO100RSB2
93	IO98RSB2
94	IO96RSB2
95	IO92RSB2
96	GDC2/IO91RSB2
97	GND
98	GDB2/IO90RSB2
99	GDA2/IO89RSB2
100	GNDQ
101	TCK
102	TDI
103	TMS
104	VMV2
105	GND
106	VPUMP
107	GNDQ
108	TDO

FG144	
Pin Number	A3P250 Function
K1	GEBO/IO99NDB3
K2	GEA1/IO98PDB3
K3	GEA0/IO98NDB3
K4	GEA2/IO97RSB2
K5	IO90RSB2
K6	IO84RSB2
K7	GND
K8	IO66RSB2
K9	GDC2/IO63RSB2
K10	GND
K11	GDA0/IO60VDB1
K12	GDB0/IO59VDB1
L1	GND
L2	VMV3
L3	GEB2/IO96RSB2
L4	IO91RSB2
L5	VCCIB2
L6	IO82RSB2
L7	IO80RSB2
L8	IO72RSB2
L9	TMS
L10	VJTAG
L11	VMV2
L12	TRST
M1	GNDQ
M2	GEC2/IO95RSB2
M3	IO92RSB2
M4	IO89RSB2
M5	IO87RSB2
M6	IO85RSB2
M7	IO78RSB2
M8	IO76RSB2
M9	TDI
M10	VCCIB2
M11	VPUMP
M12	GNDQ

FG144	
Pin Number	A3P400 Function
A1	GNDQ
A2	VMV0
A3	GAB0/IO02RSB0
A4	GAB1/IO03RSB0
A5	IO16RSB0
A6	GND
A7	IO30RSB0
A8	VCC
A9	IO34RSB0
A10	GBA0/IO58RSB0
A11	GBA1/IO59RSB0
A12	GNDQ
B1	GAB2/IO154UDB3
B2	GND
B3	GAA0/IO00RSB0
B4	GAA1/IO01RSB0
B5	IO14RSB0
B6	IO19RSB0
B7	IO23RSB0
B8	IO31RSB0
B9	GBB0/IO56RSB0
B10	GBB1/IO57RSB0
B11	GND
B12	VMV1
C1	IO154VDB3
C2	GFA2/IO144PPB3
C3	GAC2/IO153UDB3
C4	VCC
C5	IO12RSB0
C6	IO17RSB0
C7	IO25RSB0
C8	IO32RSB0
C9	IO53RSB0
C10	GBA2/IO60PDB1
C11	IO60NDB1
C12	GBC2/IO62PPB1

FG144	
Pin Number	A3P400 Function
D1	IO149NDB3
D2	IO149PDB3
D3	IO153VDB3
D4	GAA2/IO155UPB3
D5	GAC0/IO04RSB0
D6	GAC1/IO05RSB0
D7	GBC0/IO54RSB0
D8	GBC1/IO55RSB0
D9	GBB2/IO61PDB1
D10	IO61NDB1
D11	IO62NPB1
D12	GCB1/IO68PPB1
E1	VCC
E2	GFC0/IO147NDB3
E3	GFC1/IO147PDB3
E4	VCCIB3
E5	IO155VPB3
E6	VCCIB0
E7	VCCIB0
E8	GCC1/IO67PDB1
E9	VCCIB1
E10	VCC
E11	GCA0/IO69NDB1
E12	IO70NDB1
F1	GFB0/IO146NPB3
F2	VCOMPLF
F3	GFB1/IO146PPB3
F4	IO144NPB3
F5	GND
F6	GND
F7	GND
F8	GCC0/IO67NDB1
F9	GCB0/IO68NPB1
F10	GND
F11	GCA1/IO69PDB1
F12	GCA2/IO70PDB1

FG144	
Pin Number	A3P400 Function
G1	GFA1/IO145PPB3
G2	GND
G3	VCCPLF
G4	GFA0/IO145NPB3
G5	GND
G6	GND
G7	GND
G8	GDC1/IO77UPB1
G9	IO72NDB1
G10	GCC2/IO72PDB1
G11	IO71NDB1
G12	GCB2/IO71PDB1
H1	VCC
H2	GFB2/IO143PDB3
H3	GFC2/IO142PSB3
H4	GEC1/IO137PDB3
H5	VCC
H6	IO75PDB1
H7	IO75NDB1
H8	GDB2/IO81RSB2
H9	GDC0/IO77VPB1
H10	VCCIB1
H11	IO73PSB1
H12	VCC
J1	GEB1/IO136PDB3
J2	IO143NDB3
J3	VCCIB3
J4	GEC0/IO137NDB3
J5	IO125RSB2
J6	IO116RSB2
J7	VCC
J8	TCK
J9	GDA2/IO80RSB2
J10	TDO
J11	GDA1/IO79UDB1
J12	GDB1/IO78UDB1

FG256	
Pin Number	A3P400 Function
P9	IO98RSB2
P10	IO95RSB2
P11	IO88RSB2
P12	IO84RSB2
P13	TCK
P14	VPUMP
P15	TRST
P16	GDA0/IO79VDB1
R1	GEA1/IO135PDB3
R2	GEA0/IO135NDB3
R3	IO127RSB2
R4	GEC2/IO132RSB2
R5	IO123RSB2
R6	IO118RSB2
R7	IO112RSB2
R8	IO106RSB2
R9	IO100RSB2
R10	IO96RSB2
R11	IO89RSB2
R12	IO85RSB2
R13	GDB2/IO81RSB2
R14	TDI
R15	NC
R16	TDO
T1	GND
T2	IO126RSB2
T3	GEB2/IO133RSB2
T4	IO124RSB2
T5	IO116RSB2
T6	IO113RSB2
T7	IO107RSB2
T8	IO105RSB2
T9	IO102RSB2
T10	IO97RSB2
T11	IO92RSB2
T12	GDC2/IO82RSB2

FG256	
Pin Number	A3P400 Function
T13	IO86RSB2
T14	GDA2/IO80RSB2
T15	TMS
T16	GND

FG256	
Pin Number	A3P600 Function
G13	GCC1/IO69PPB1
G14	IO65NPB1
G15	IO75PDB1
G16	IO75NDB1
H1	GFB0/IO163NPB3
H2	GFA0/IO162NDB3
H3	GFB1/IO163PPB3
H4	VCOMPLF
H5	GFC0/IO164NPB3
H6	VCC
H7	GND
H8	GND
H9	GND
H10	GND
H11	VCC
H12	GCC0/IO69NPB1
H13	GCB1/IO70PPB1
H14	GCA0/IO71NPB1
H15	IO67NPB1
H16	GCB0/IO70NPB1
J1	GFA2/IO161PPB3
J2	GFA1/IO162PDB3
J3	VCCPLF
J4	IO160NDB3
J5	GFB2/IO160PDB3
J6	VCC
J7	GND
J8	GND
J9	GND
J10	GND
J11	VCC
J12	GCB2/IO73PPB1
J13	GCA1/IO71PPB1
J14	GCC2/IO74PPB1
J15	IO80PPB1
J16	GCA2/IO72PDB1

FG256	
Pin Number	A3P600 Function
K1	GFC2/IO159PDB3
K2	IO161NPB3
K3	IO156PPB3
K4	IO129RSB2
K5	VCCIB3
K6	VCC
K7	GND
K8	GND
K9	GND
K10	GND
K11	VCC
K12	VCCIB1
K13	IO73NPB1
K14	IO80NPB1
K15	IO74NPB1
K16	IO72NDB1
L1	IO159NDB3
L2	IO156NPB3
L3	IO151PPB3
L4	IO158PSB3
L5	VCCIB3
L6	GND
L7	VCC
L8	VCC
L9	VCC
L10	VCC
L11	GND
L12	VCCIB1
L13	GDB0/IO87NPB1
L14	IO85NDB1
L15	IO85PDB1
L16	IO84PDB1
M1	IO150PDB3
M2	IO151NPB3
M3	IO147NPB3
M4	GEC0/IO146NPB3

FG256	
Pin Number	A3P600 Function
M5	VMV3
M6	VCCIB2
M7	VCCIB2
M8	IO117RSB2
M9	IO110RSB2
M10	VCCIB2
M11	VCCIB2
M12	VMV2
M13	IO94RSB2
M14	GDB1/IO87PPB1
M15	GDC1/IO86PDB1
M16	IO84NDB1
N1	IO150NDB3
N2	IO147PPB3
N3	GEC1/IO146PPB3
N4	IO140RSB2
N5	GNDQ
N6	GEA2/IO143RSB2
N7	IO126RSB2
N8	IO120RSB2
N9	IO108RSB2
N10	IO103RSB2
N11	IO99RSB2
N12	GNDQ
N13	IO92RSB2
N14	VJTAG
N15	GDC0/IO86NDB1
N16	GDA1/IO88PDB1
P1	GEB1/IO145PDB3
P2	GEB0/IO145NDB3
P3	VMV2
P4	IO138RSB2
P5	IO136RSB2
P6	IO131RSB2
P7	IO124RSB2
P8	IO119RSB2

Revision	Changes	Page
Revision 13 (January 2013)	The "ProASIC3 Ordering Information" section has been updated to mention "Y" as "Blank" mentioning "Device Does Not Include License to Implement IP Based on the Cryptography Research, Inc. (CRI) Patent Portfolio" (SAR 43104).	1-IV
	Added a note to Table 2-2 • Recommended Operating Conditions 1 (SAR 43644): The programming temperature range supported is $T_{\text{ambient}} = 0^{\circ}\text{C}$ to 85°C .	2-2
	The note in Table 2-115 • ProASIC3 CCC/PLL Specification referring the reader to SmartGen was revised to refer instead to the online help associated with the core (SAR 42569).	2-90
	Libero Integrated Design Environment (IDE) was changed to Libero System-on-Chip (SoC) throughout the document (SAR 40284). Live at Power-Up (LAPU) has been replaced with 'Instant On'.	NA
Revision 12 (September 2012)	The Security section was modified to clarify that Microsemi does not support read-back of programmed data.	1-1
	Added a Note stating "VMV pins must be connected to the corresponding VCCI pins. See the "VMVx I/O Supply Voltage (quiet)" section on page 3-1 for further information" to Table 2-1 • Absolute Maximum Ratings and Table 2-2 • Recommended Operating Conditions 1 (SAR 38321).	2-1 2-2
	Table 2-35 • Duration of Short Circuit Event Before Failure was revised to change the maximum temperature from 110°C to 100°C , with an example of six months instead of three months (SAR 37933).	2-31
	In Table 2-93 • Minimum and Maximum DC Input and Output Levels, VIL and VIH were revised so that the maximum is 3.6 V for all listed values of VCCI (SAR 28549).	2-68
	Figure 2-37 • FIFO Read and Figure 2-38 • FIFO Write are new (SAR 28371).	2-99
	The following sentence was removed from the "VMVx I/O Supply Voltage (quiet)" section in the "Pin Descriptions" chapter: "Within the package, the VMV plane is decoupled from the simultaneous switching noise originating from the output buffer VCCI domain" and replaced with "Within the package, the VMV plane biases the input stage of the I/Os in the I/O banks" (SAR 38321). The datasheet mentions that "VMV pins must be connected to the corresponding VCCI pins" for an ESD enhancement.	3-1